



March 2016

FQB34P10

P-Channel QFET[®] MOSFET

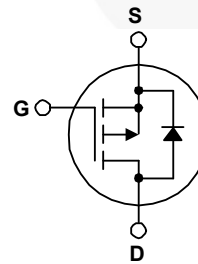
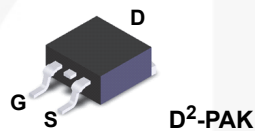
100 V, -33.5 A, 60 mΩ

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -33.5 A, -100 V, $R_{DS(on)} = 60 \text{ m}\Omega$ (Max.) @ $V_{GS} = .10 \text{ V}$, $I_D = -16.75 \text{ A}$
- Low Gate Charge (Typ. 85 nC)
- Low C_{rss} (Typ. 170 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



Absolute Maximum Ratings

 $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQB34P10TM	Unit
V_{DSS}	Drain-Source Voltage	-100	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	-33.5	A
	- Continuous ($T_C = 100^\circ\text{C}$)	-23.5	A
I_{DM}	Drain Current - Pulsed (Note 1)	-134	A
V_{GSS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	2200	mJ
I_{AR}	Avalanche Current (Note 1)	-33.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	15.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-6.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.75	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	155	W
	- Derate above 25°C	1.03	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQB34P10TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.97	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB34P10TM	FQB34P10	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C	--	-0.1	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
		$V_{DS} = -80\text{ V}, T_C = 150^\circ\text{C}$	--	--	-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -16.75\text{ A}$	--	0.049	0.06	Ω
g_{FS}	Forward Transconductance	$V_{DS} = -40\text{ V}, I_D = -16.75\text{ A}$	--	23	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2240	2910	pF
C_{oss}	Output Capacitance		--	730	950	pF
C_{rss}	Reverse Transfer Capacitance		--	170	220	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -50\text{ V}, I_D = -33.5\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4)	--	25	60	ns
t_r	Turn-On Rise Time		--	250	510	ns
$t_{d(off)}$	Turn-Off Delay Time		--	160	330	ns
t_f	Turn-Off Fall Time		--	210	430	ns
Q_g	Total Gate Charge	$V_{DS} = -80\text{ V}, I_D = -33.5\text{ A},$ $V_{GS} = -10\text{ V}$ (Note 4)	--	85	110	nC
Q_{gs}	Gate-Source Charge		--	15	--	nC
Q_{gd}	Gate-Drain Charge		--	45	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	-33.5	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-134	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -33.5 A	--	--	-4.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -33.5 A,	--	160	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	--	0.88	--	μC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = \text{mH}, I_{AS} = -33.5\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq -33.5\text{ A}, dI/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

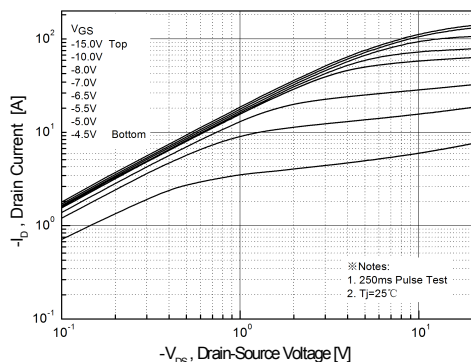


Figure 1. On-Region Characteristics

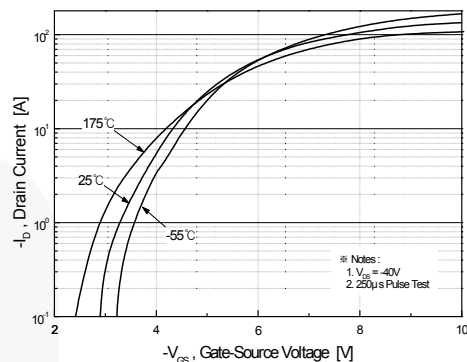


Figure 2. Transfer Characteristics

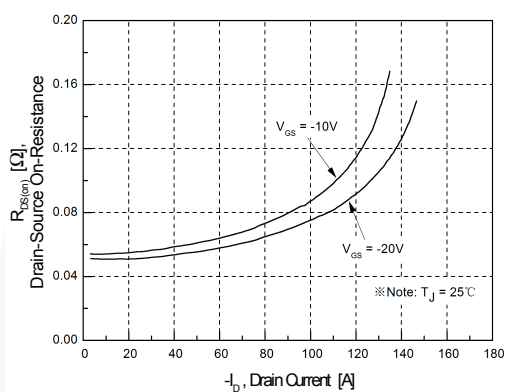


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

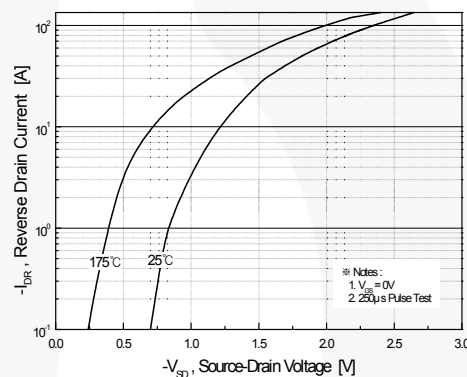


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

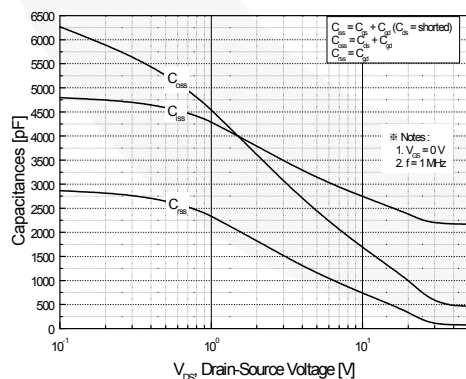


Figure 5. Capacitance Characteristics

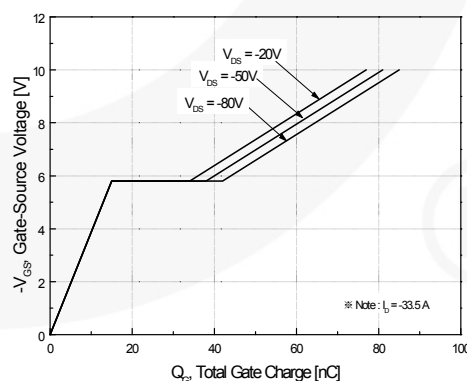


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

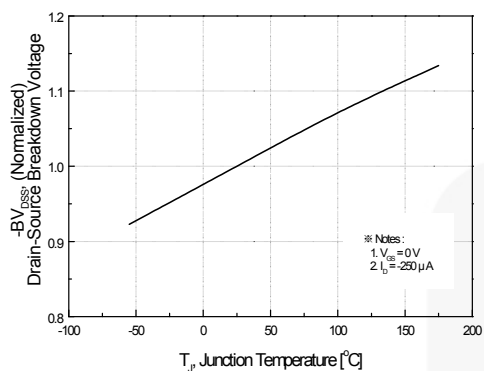


Figure 7. Breakdown Voltage Variation vs. Temperature

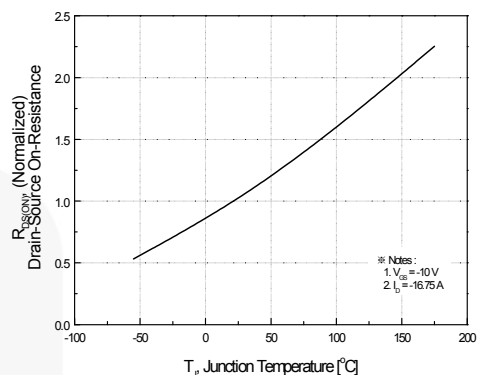


Figure 8. On-Resistance Variation vs. Temperature

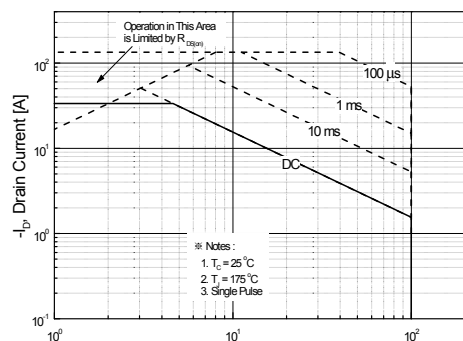


Figure 9. Maximum Safe Operating Area

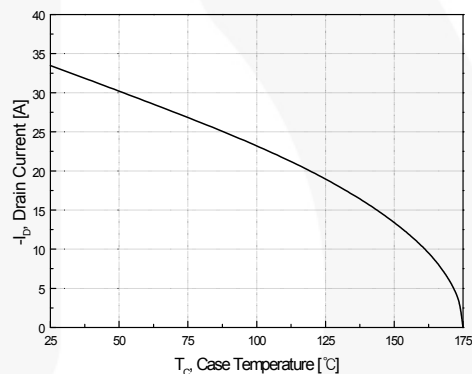


Figure 10. Maximum Drain Current vs. Case Temperature

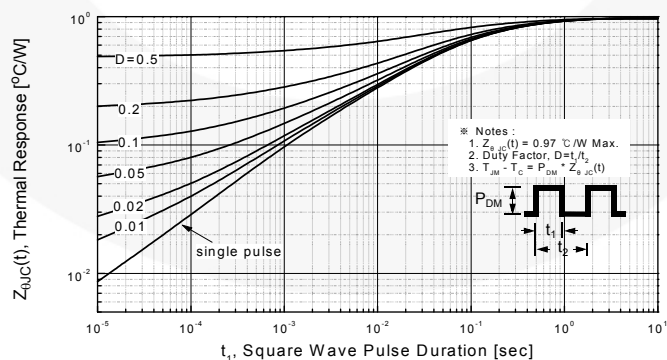


Figure 11. Transient Thermal Response Curve

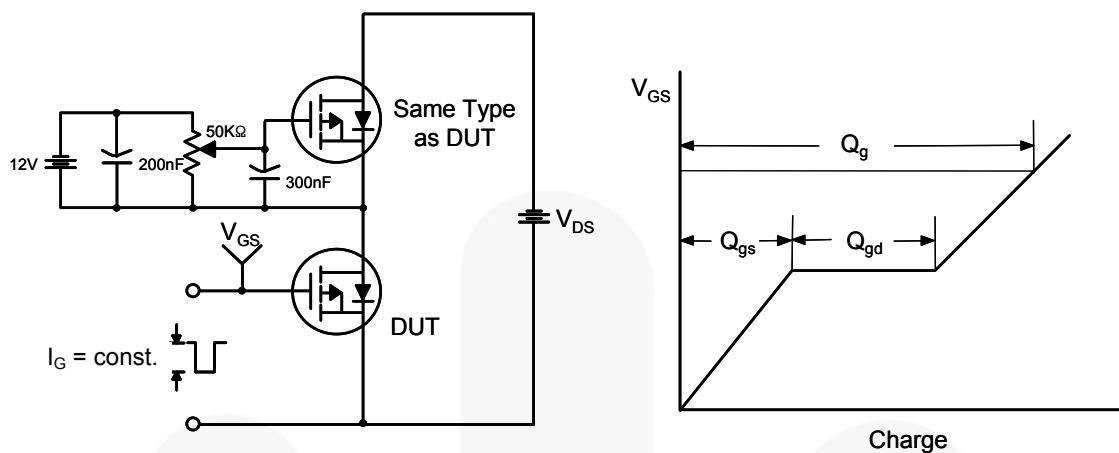


Figure 12. Gate Charge Test Circuit & Waveform

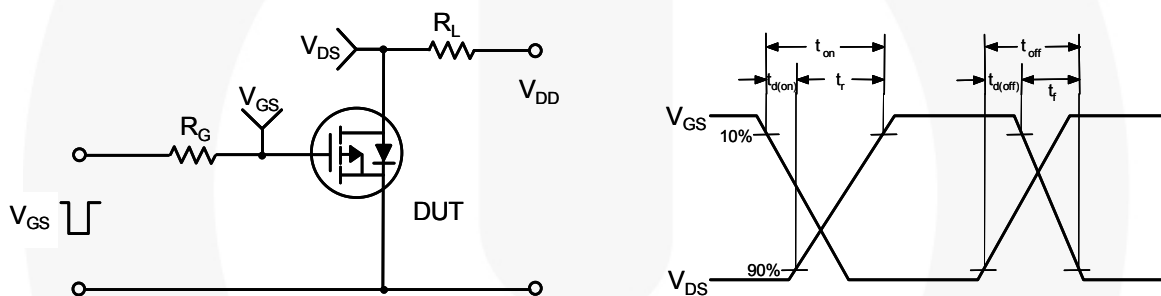


Figure 13. Resistive Switching Test Circuit & Waveforms

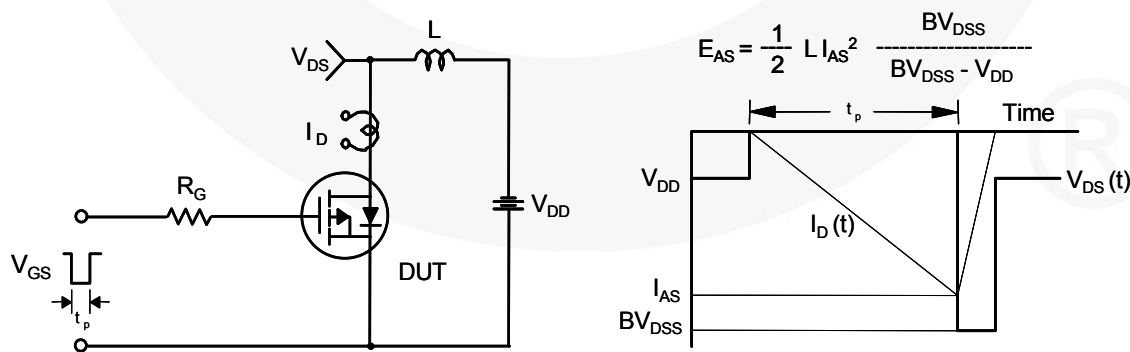
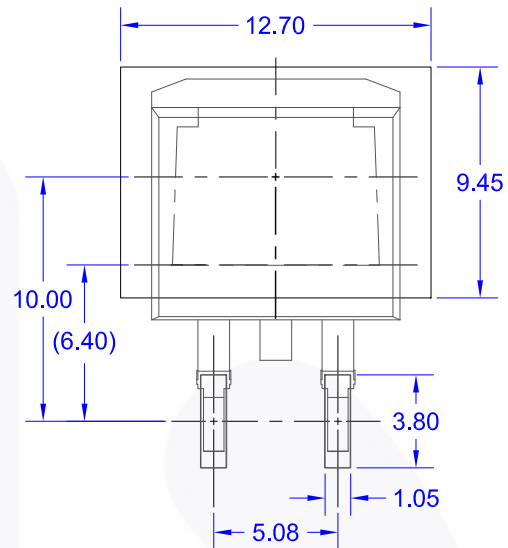
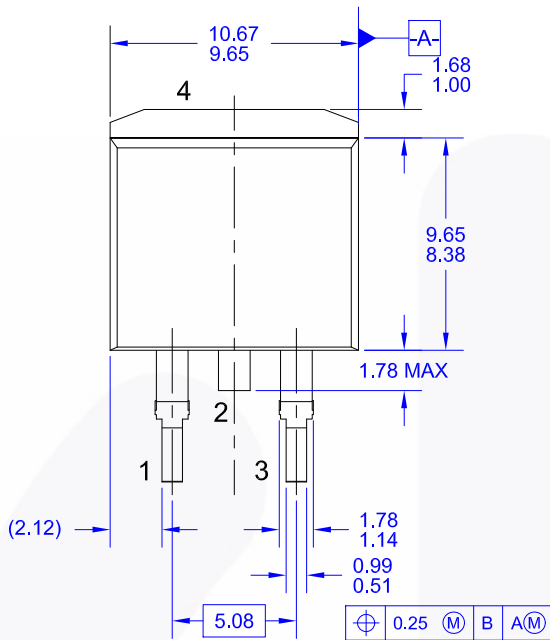
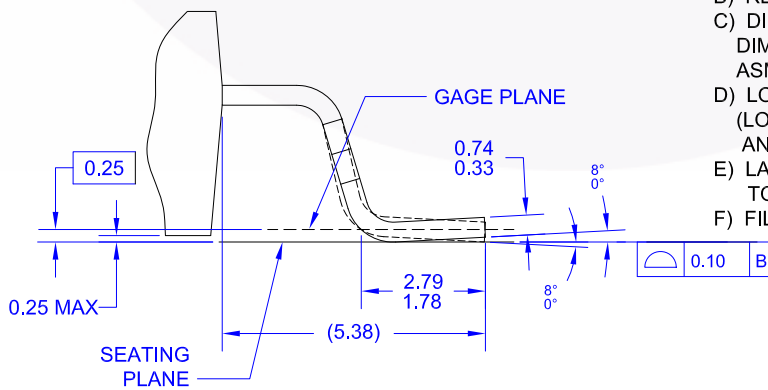
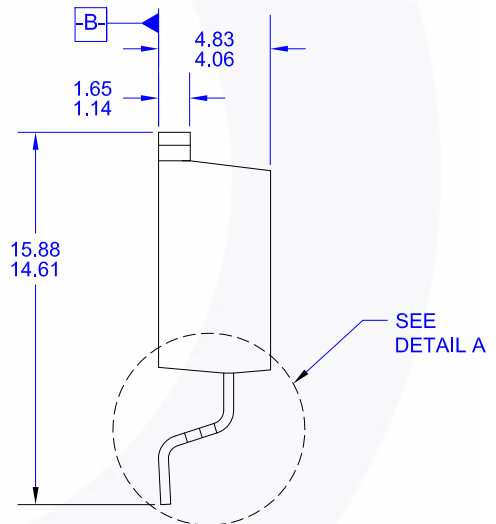
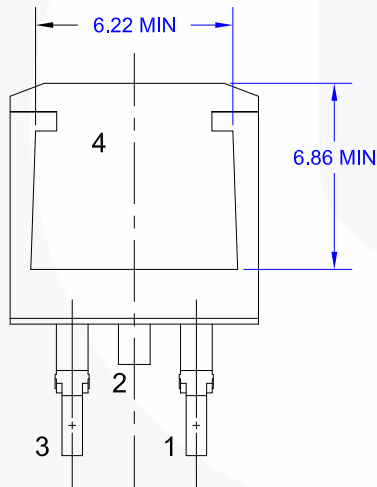


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

Mechanical Dimensions



LAND PATTERN RECOMMENDATION
UNLESS NOTED, ALL DIMS TYPICAL



DETAIL A, ROTATED 90°
SCALE: 2X

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) REFERENCE JEDEC, TO-263, VARIATION AB.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
 - D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
 - E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
 - F) FILENAME: TO263A02REV7





**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower[™]
AttitudeEngine[™]
Awinda[®]
AX-CAP[®]
BitSiC[™]
Build it Now[™]
CorePLUS[™]
CorePOWER[™]
CROSSVOLT[™]
CTL[™]
Current Transfer Logic[™]
DEUXPEED[®]
Dual Cool[™]
EcoSPARK[®]
EfficientMax[™]
ESBC[™]


Fairchild[®]
Fairchild Semiconductor[®]
FACT Quiet Series[™]
FACT[®]
FastvCore[™]
FETBench[™]
FPS[™]

F-PFST[™]
FRFET[®]
Global Power ResourceSM
GreenBridge[™]
Green FPS[™]
Green FPS[™] e-Series[™]
Gmax[™]
GTO[™]
IntelliMAX[™]
ISOPLANAR[™]
Marking Small Speakers Sound Louder
and Better[™]
MegaBuck[™]
MICROCOUPLER[™]
MicroFET[™]
MicroPak[™]
MicroPak2[™]
MillerDrive[™]
MotionMax[™]
MotionGrid[®]
MT[®]
MTx[®]
MVN[®]
mWSaver[®]
OptoHiT[™]
OPTOLOGIC[®]

OPTOPLANAR[®]

Power Supply WebDesigner[™]
PowerTrench[®]
PowerXS[™]
Programmable Active Droop[™]
QFET[®]
QS[™]
Quiet Series[™]
RapidConfigure[™]

Saving our world, 1mW/W/kW at a time[™]
SignalWise[™]
SmartMax[™]
SMART START[™]
Solutions for Your Success[™]
SPM[®]
STEALTH[™]
SuperFET[®]
SuperSOT[™]-3
SuperSOT[™]-6
SuperSOT[™]-8
SupreMOS[®]
SyncFET[™]
Sync-Lock[™]


TinyBoost[®]
TinyBuck[®]
TinyCalc[™]
TinyLogic[®]
TINYOPTO[™]
TinyPower[™]
TinyPWM[™]
TinyWire[™]
TranSiC[™]
TriFault Detect[™]
TRUECURRENT[®]
μSerDes[™]

UHC[®]
Ultra FRFET[™]
UniFET[™]
VCX[™]
VisualMax[™]
VoltagePlus[™]
XS[™]
Xsens[™]
仙童[®]

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT [HTTP://WWW.FAIRCHILDSEMI.COM](http://www.fairchildsemi.com). FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use. Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 177

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative